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October 6, 2003

To: Commissioner for Patents P.O.Box 1450 Alexandria, VA 22313-1450

Fr: George O. Saile, Reg. No. 19,572 28 Davis Avenue Poughkeepsie, N.Y. 12603

Subject:

Serial No. 10/615,745 07/09/03

Amos Chou et al.

A NOVEL BIOLOGICAL APPROACH FOR FORMING LOW-K DIELECTRICS

Grp. Art Unit:

INFORMATION DISCLOSURE STATEMENT

Enclosed is Form PTO-1449, Information Disclosure Citation In An Application.

The following Patents and/or Publications are submitted to comply with the duty of disclosure under CFR 1.97-1.99 and 37 CFR 1.56. Copies of each document is included herewith.

CERTIFICATE OF MAILING

I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail in an envelope addressed to: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450, on October [0], 2003.

Stephen B. Ackerman, Reg.# 37761

Signature/Date

TSMC-01-1004

- U.S. Patent 6,204,202 to Leung et al., "Low Dielectric Constant Porous Films," teaches a method for forming porous films of low dielectric constant, specifically nanoporous silica films.
- U.S. Patent 6,159,842 to Chang et al., "Method for Fabricating a Hybrid Low-Dielectric-Constant Intermetal Dielectric (IMD) Layer with Improved Reliability for Multilevel Interconnections," teaches a method for fabricating a low-k intermetal dieletric layer by first covering the metal lines with a protective low-k fluorine doped oxide, filling the lined gaps so formed with a porous, spun-on dielectric layer, then covering the entire structure with a more dense dielectric layer to provide the needed structural integrity.
- U.S. Patent 6,265,321 to Chooi et al., "Air Bridge Process for Forming Air Gaps," teaches a method for confining air-plugs between metal interconnects.
- U.S. Patent 5,171,713 to Matthews, "Process for Forming Planarized, Air-Bridge Interconnects on a Semiconductor Substrate," teaches the fabrication of a multilevel integrated circuit in which successively formed levels are separated by polyimide layers through which interconnects pass.

Stephen B. Ackerman, Reg. #37761

Sincerely

Form PTO-1449 10/615,745 TSMC-01-1004 INFORMATION DISCLOSURE CITATION IN AN APPLICATION שאט את שאו Usia soveral shouts il nocessary) U. S. PATENT DOCUMENTS ያፕአሀቂዕክቲሊ ነ CLUE MACULA HULL DOCUMENT HUMBER DATE 438 FOREIGN PATENT DOCUMENTS Translation CUSS ಉಂದಿ COUNTRY OUTE DOCUMENT NUMBER YES NO OTHER DOCUMENTS (Induding Luthor, Title, Date, Pertinent Pages, Etc.) DATE CONCOERED

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant

EXAMINER